Abstract Submitted
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Modification of a scanning electron microscope (SEM) for insitu, nanometer size contact, electrical measurements of III-nitride transistors CAMELIA SELCU, Department of Physics, The Ohio State University, ZHICHAO YANG, SRIRAM KRISHNAMOORTHY, SIDDHARTH RAJAN, Department of Electrical and Computer Engineering, The Ohio State University — As the transistors become smaller and smaller, proximity effects become important, therefore there is a need for characterization instruments. We modified a scanning electron microscope (SEM) by adding the capability to make mechanical contacts to devices for electrical measurements with nanometer precision. We will discuss ongoing work involving III-nitride transistors and nanowires.

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